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Kind regards,

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# 2N7002PT

# 60 V, 310 mA N-channel Trench MOSFET Rev. 1 — 2 July 2010

Product data sheet

## **Product profile**

## 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT416 (SC-75) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

## 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_{amb} = 25  ^{\circ}C$	-	-	60	V
$V_{GS}$	gate-source voltage	$T_{amb} = 25  ^{\circ}C$	-	-	±20	V
$I_D$	drain current	$T_{amb}$ = 25 °C; $V_{GS}$ = 10 V	[1] -	-	310	mA
R <sub>DSon</sub>	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 500 \text{mA}$	-	1	1.6	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## 60 V, 310 mA N-channel Trench MOSFET

## 2. Pinning information

Table 2. Pinning

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source	-3	
3	D	drain	1 2	G

# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
2N7002PT	SC-75	plastic surface-mounted package; 3 leads	SOT416	

## 4. Marking

Table 4. Marking codes

Type number	Marking code
2N7002PT	Z1

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

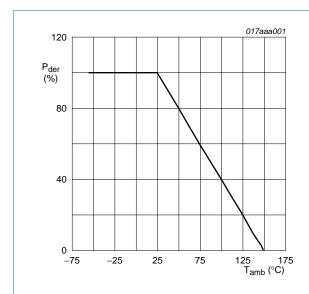
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_{amb} = 25  ^{\circ}C$	-	60	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	±20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V	<u>[1]</u>		
		T <sub>amb</sub> = 25 °C	-	310	mA
		T <sub>amb</sub> = 100 °C	-	240	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

## 60 V, 310 mA N-channel Trench MOSFET

**Table 5.** Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

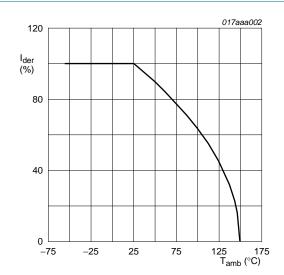
Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	250	mW
			[1]	300	mW
		T <sub>sp</sub> = 25 °C	-	770	mW
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C
Source-d	rain diode				
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	310	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

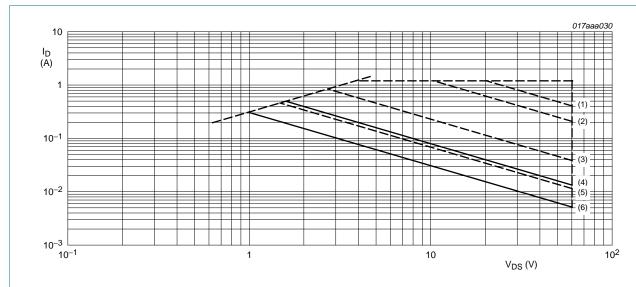
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

## 60 V, 310 mA N-channel Trench MOSFET



I<sub>DM</sub> = single pulse

- (1)  $t_p = 100 \mu s$
- (2)  $t_p = 1 \text{ ms}$
- (3)  $t_p = 10 \text{ ms}$
- (4) DC;  $T_{sp} = 25 \, ^{\circ}C$
- (5)  $t_p = 100 \text{ ms}$
- (6) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 1 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

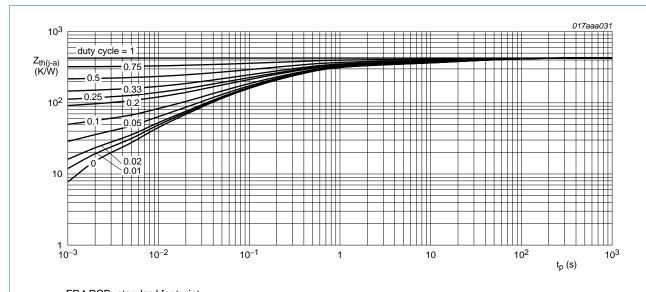
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> _	440	510	K/W
	junction to ambient		[2] _	360	415	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	160	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

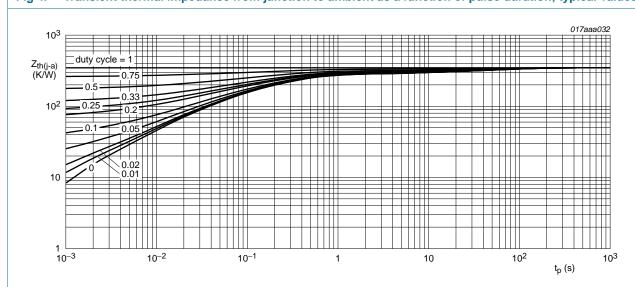
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

#### 60 V, 310 mA N-channel Trench MOSFET



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 60 V, 310 mA N-channel Trench MOSFET

## 7. Characteristics

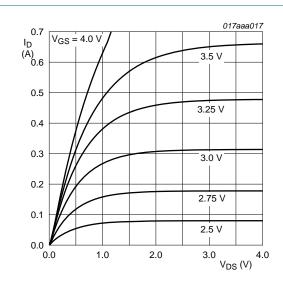
**Table 7. Characteristics** 

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T <sub>j</sub> = 25 °C	-	-	1	μΑ
		T <sub>j</sub> = 150 °C	-	-	10	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
$R_{DSon}$	drain-source on-state resistance		<u>[1]</u>			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 500 \text{ mA}$	-	1	1.6	Ω
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	<u>[1]</u> _	400	-	mS
Dynamic (	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 300 \text{ mA};$	-	0.6	8.0	nC
$Q_{GS}$	gate-source charge	V <sub>DS</sub> = 30 V; - V <sub>GS</sub> = 4.5 V	-	0.2	-	nC
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 4.5 V	-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	30	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DD</sub> = 50 V;	-	3	6	ns
t <sub>r</sub>	rise time	$R_L = 250 \Omega;$ - V <sub>GS</sub> = 10 V;	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time	$R_{G} = 6 \Omega$	-	10	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

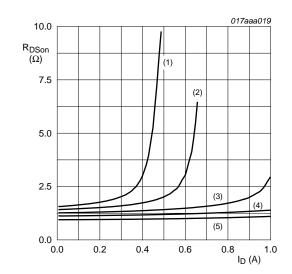
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.01.$ 

## 60 V, 310 mA N-channel Trench MOSFET



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T<sub>amb</sub> = 25 °C

(1)  $V_{GS} = 3.25 \text{ V}$ 

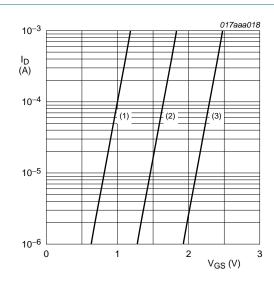
(2)  $V_{GS} = 3.5 \text{ V}$ 

(3)  $V_{GS} = 4 V$ 

(4)  $V_{GS} = 5 V$ 

(5)  $V_{GS} = 10 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



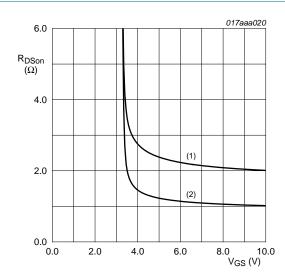
 $T_{amb}$  = 25 °C;  $V_{DS}$  = 5 V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 500 \text{ mA}$ 

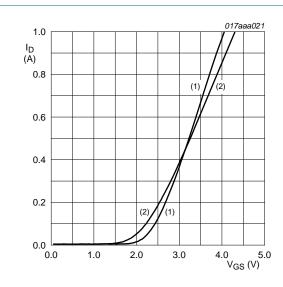
(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

2N7002PT

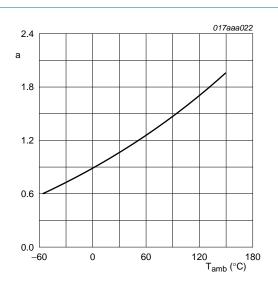
#### 60 V, 310 mA N-channel Trench MOSFET



$$V_{DS} > I_D \times R_{DSon}$$

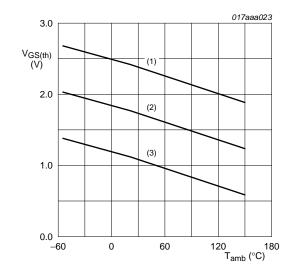
- (1)  $T_{amb} = 25 \, ^{\circ}C$
- (2)  $T_{amb} = 150 \, ^{\circ}C$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

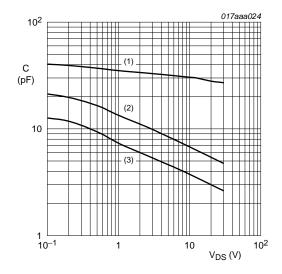
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of ambient temperature

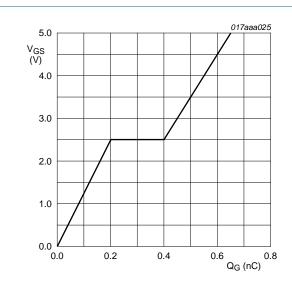


f = 1 MHz; V<sub>GS</sub> = 0 V

- (1) C<sub>iss</sub>
- (2) Coss
- $(3) \quad C_{rss}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

## 60 V, 310 mA N-channel Trench MOSFET



 $I_D$  = 300 mA;  $V_{DS}$  = 30 V;  $T_{amb}$  = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

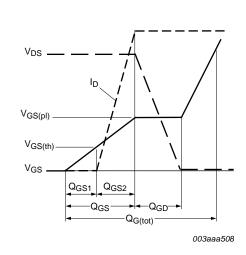
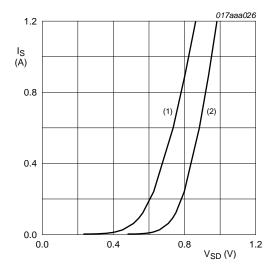


Fig 15. Gate charge waveform definitions



$$V_{GS} = 0 V$$

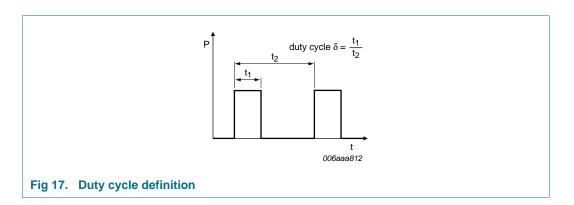
Fig 16. Source current as a function of source-drain voltage; typical values

<sup>(1)</sup>  $T_{amb} = 150 \, ^{\circ}C$ 

<sup>(2)</sup>  $T_{amb} = 25 \, ^{\circ}C$ 

60 V, 310 mA N-channel Trench MOSFET

## 8. Test information



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 60 V, 310 mA N-channel Trench MOSFET

## 9. Package outline

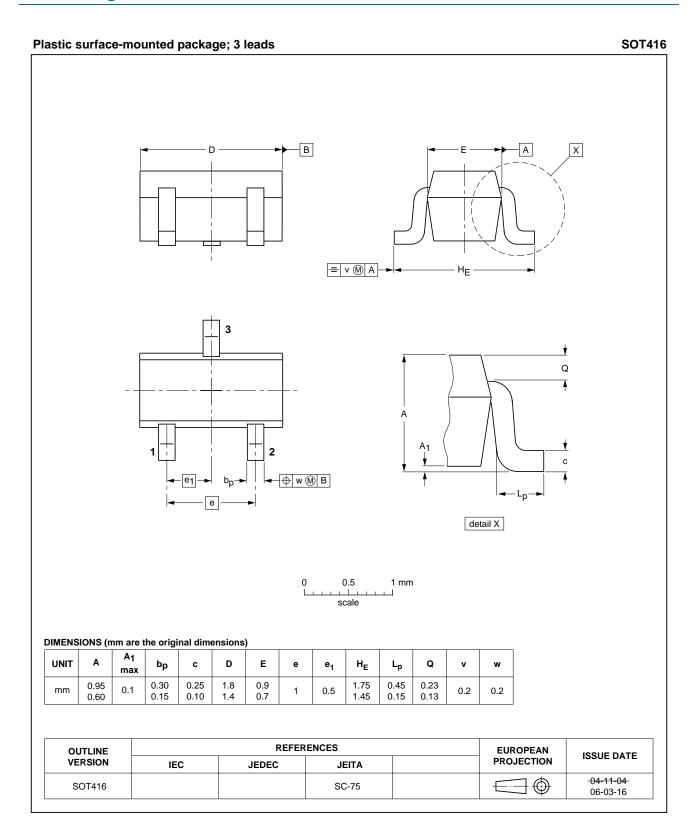


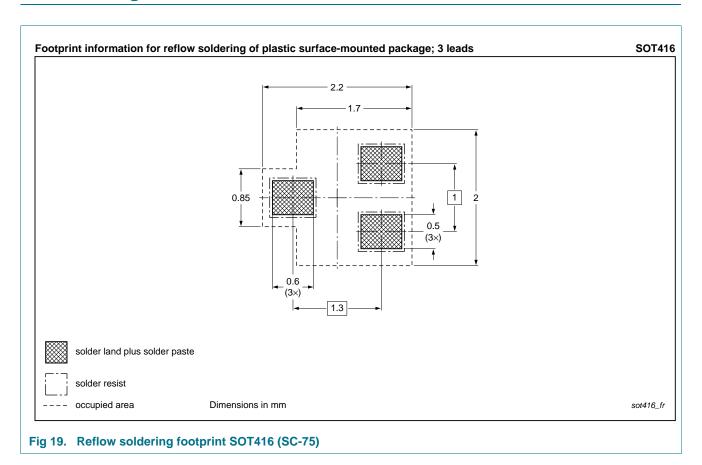
Fig 18. Package outline SOT416 (SC-75)

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60 V, 310 mA N-channel Trench MOSFET

## 10. Soldering



## 60 V, 310 mA N-channel Trench MOSFET

# 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002PT v.1	20100702	Product data sheet	-	-

#### 60 V, 310 mA N-channel Trench MOSFET

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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## 60 V, 310 mA N-channel Trench MOSFET

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2N7002PT **NXP Semiconductors** 

## 60 V, 310 mA N-channel Trench MOSFET

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